

1N4009/FDLL4009

Ultra High Speed Diodes

7.03.09

• trr...2 ns (MAX)

• BV...35 V (MIN) @ 5 μA

PACKAGES

1N4009

DO-35

FDLL4009

LL-34

ABSOLUTE MAXIMUM RATINGS (Note 1)

Temperatures

Storage Temperature Range

Maximum Junction Operating Temperature

Lead Temperature

-65°C to +200°C +175°C +260°C If you need this device in the SOT package, an electical equivalent is available. See FDSO1200 family.

Power Dissipation (Note 2)

Maximum Total Power Dissipation at 25°C Ambient Linear Power Derating Factor

500 mW 3.33 mW/°C

Maximum Voltage and Current

Working Inverse Voltage Average Rectified Current WIV lo IF Continuous Forward Current Peak Repetitive Forward Current Peak Forward Surge Current if (surge) Pulse Width = 1 s Pulse Width = $1 \mu s$

100 mA 300 mA 400 mA 1.0 A 4.0 A

25 V

ICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	MAX	UNITS	TEST CONDITIONS
VF	Forward Voltage		1.0	٧	1F = 30 mA
I _R	Reverse Current		0.1 100	μA μA	V _R = 25 V V _R = 25 V, T _A = 150°C
BV	Breakdown Voltage	35		V	i _R = 5.0 μA
trr	Reverse Recovery Time		4.0 2.0	ns ns	$I_f = I_r = 10 \text{ mA (Note 3)}$ $I_f = 10 \text{ mA, } V_r = 6.0 \text{ V,}$ $R_L = 100 \Omega$
С	Capacitance		4,0	pF	V _R = 0,f = 1,0 MHz

NOTES:

1. These ratings are limiting values above which the serviceability of the diode may be impaired.

2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty-cycle operation.

3. Recovery to 1.0 mA.

4. For product family characteristic curves, refer to Chapter 4, D4